

N-channel 40 V, 2.0 mΩ standard level MOSFET in LFPAK56 9 May 2018 Product data sheet

### 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

### 2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower R<sub>DSon</sub> in same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight V<sub>GS(th)</sub> limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - · Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced R<sub>th</sub> and R<sub>DSon</sub>
  - · Increases maximum current capability and improved current spreading

#### 3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C	-	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	217	W

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#### N-channel 40 V, 2.0 m $\Omega$ standard level MOSFET in LFPAK56

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static charac	teristics					_
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	1.07	1.53	2	mΩ
Dynamic cha	racteristics					
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 25 A; $V_{DS}$ = 32 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	-	10.8	27.3	nC
Source-drain	diode					
Q <sub>r</sub>	recovered charge	$    I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \overline{\text{Fig. 16}} $	-	21	-	nC
S	softness factor	$    I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}; \text{ Fig. 16} $	-	0.8	-	

### 5. Pinning information

Table 2. Pinning	information
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Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	ل <del>ا دے ب</del> ا	
3	S	source	q	G
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	LFPAK56; Power- SO8 (SOT669)	

# 6. Ordering information

Table 3. Ordering information							
Type number	Package	'ackage					
	Name	Description	Version				
BUK7Y2R0-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669				

### 7. Marking

Table 4. Marking co	des
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Type number	Marking code
BUK7Y2R0-40H	72H040

### 8. Limiting values

#### Table 5. Limiting values

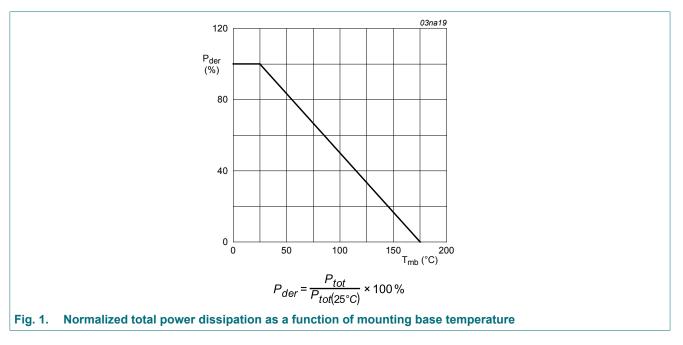
In accordance with the Absolute Maximum Rating System (IEC 60134).

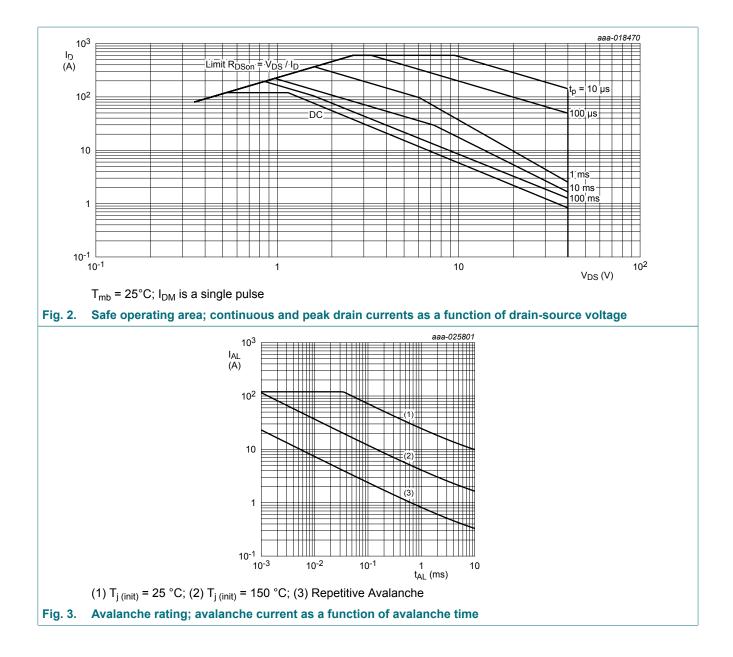
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	217	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C		-	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 2		-	600	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode			•		
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	600	А
Avalanche r	uggedness			•		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 120 \text{ A};  V_{sup} \leq 40 \text{ V};  \text{R}_{GS} = 50  \Omega; \\        $	[2] [3]	-	108	mJ

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

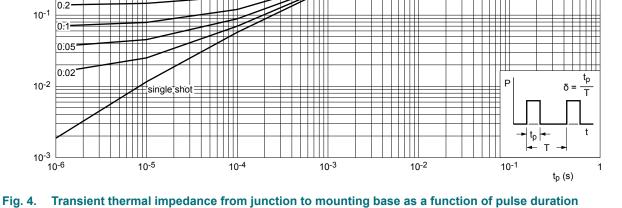
[3] Refer to application note AN10273 for further information.





### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.5	0.69	K/W
Z <sub>th(i-mb)</sub> (K/W)					a-018471	

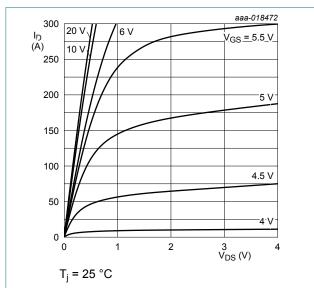


### **10. Characteristics**

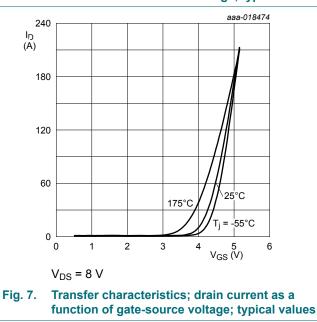
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	42.7	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C	-	40.3	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	39.7	-	V
()	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 8</u> ; Fig. 9	2.4	3	3.6	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 8</u>	-	-	4.3	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 8</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.2	1	μA
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	2	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	180	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source resistance	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 10	1.07	1.53	2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 11	1.52	2.33	3.18	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 11	1.68	2.59	3.5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11	2.11	3.24	4.36	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.36	0.9	2.3	Ω
Dynamic ch	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	52.6	90.5	nC
Q <sub>GS</sub>	gate-source charge	Fig. 12; Fig. 13	-	14.8	22.5	nC
Q <sub>GD</sub>	gate-drain charge	1 [	-	10.8	27.3	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	3633	5450	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	984	1377	pF
C <sub>rss</sub>	reverse transfer capacitance		-	188	415	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.5 Ω; V <sub>GS</sub> = 10 V;	-	13.5	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	12	-	ns
t <sub>d(off)</sub>	turn-off delay time	1 [	-	31.4	-	ns
t <sub>f</sub>	fall time	1 1	-	15.1	-	ns
Source-drai	n diode		1			-1
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C; <u>Fig. 15</u>	-	0.8	1.2	V

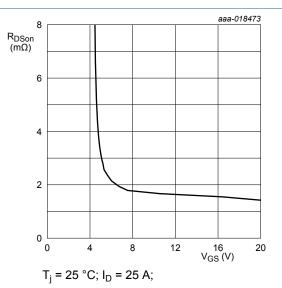
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	29	-	ns
Qr	recovered charge	V <sub>DS</sub> = 20 V; <u>Fig. 16</u>		-	21	-	nC
S	softness factor	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16}$		-	0.8	-	
		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16}$		-	0.7	-	

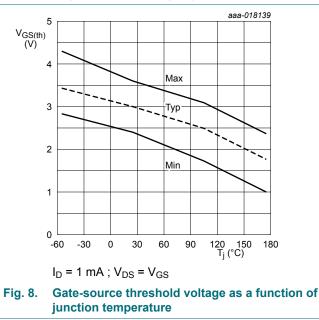


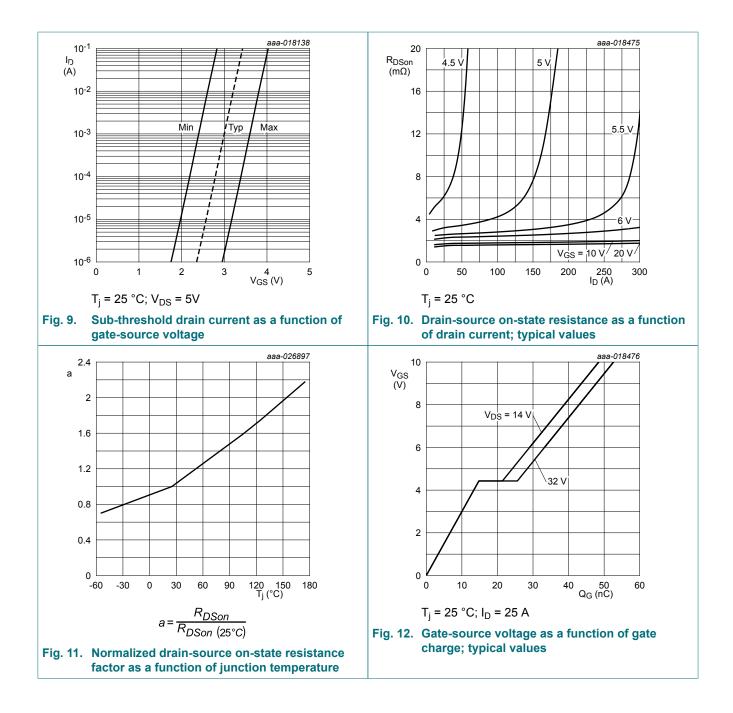


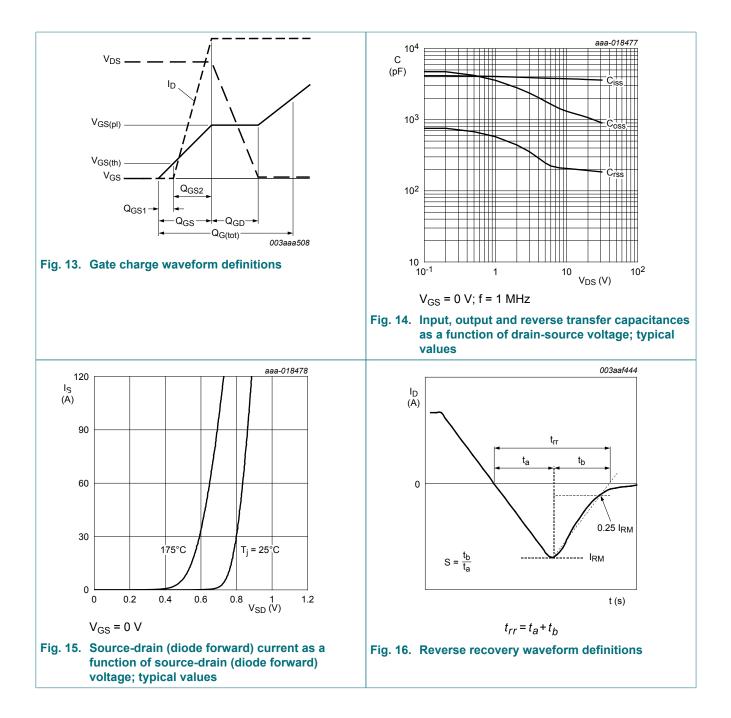




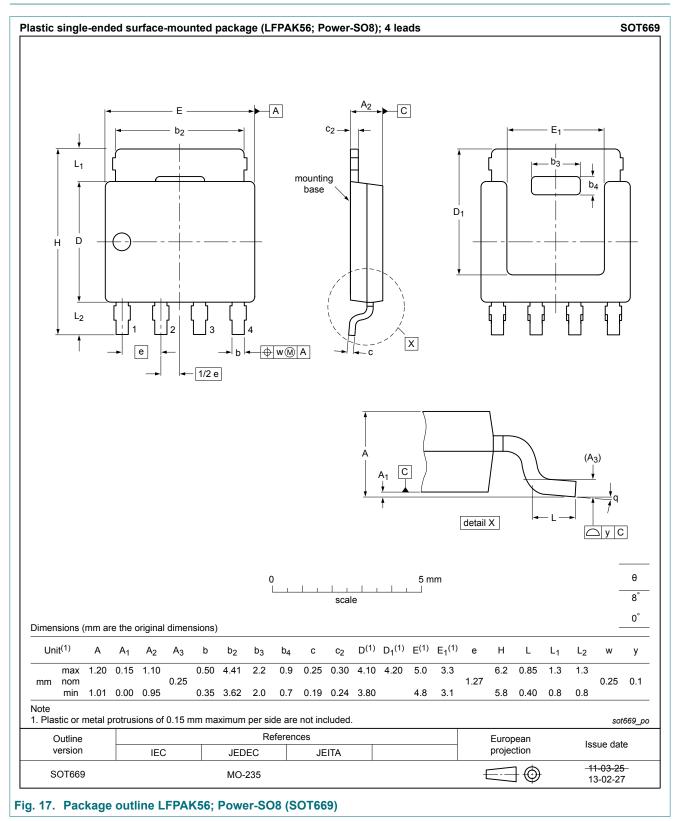








### **11. Package outline**



BUK7Y2R0-40H

#### N-channel 40 V, 2.0 m $\Omega$ standard level MOSFET in LFPAK56

### 12. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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